

LISTING OF CLAIMS

The list of claims provided below replaces all prior versions and lists of claims in the application.

Please amend the claims as follows.

1-9 (Canceled)

10. (original): A method for improved wafer planarization in a chemical mechanical planarization (CMP) process, comprising the operations of:

adjusting pressure to a polishing belt utilizing a platen having an inner set of pressure sub regions disposed below a wafer and within a circumference of the wafer; and

adjusting pressure to the polishing belt utilizing an outer set of pressure sub regions of the platen, the outer set of pressure sub regions being disposed below the wafer and outside the circumference of the wafer, the outer set of pressure sub regions being further capable of shaping the polishing pad to achieve a particular removal rate.

11. (original): A method as recited in claim 10, wherein the outer set of sub regions includes a first outer sub region and a second outer sub region.

12. (original): A method as recited in claim 11, further comprising the operation of independently adjusting the pressure provided by the first outer sub region and the second outer sub region.

13. (original): A method as recited in claim 10, further comprising the operation of independently adjusting pressure provided in a leading zone and a trailing zone of the platen, each of the leading zone and the trailing zone including an inner set of pressure sub regions and an outer set of pressure sub regions.

14. (original): A method as recited in claim 13, wherein the outer set of sub regions of each of the leading zone and the trailing zone includes a first outer sub region and a second outer sub region.

15. (original): A method as recited in claim 14, further comprising the operation of independently adjusting pressure provided by the first outer sub region and the second outer sub region.

16-22 (Canceled)